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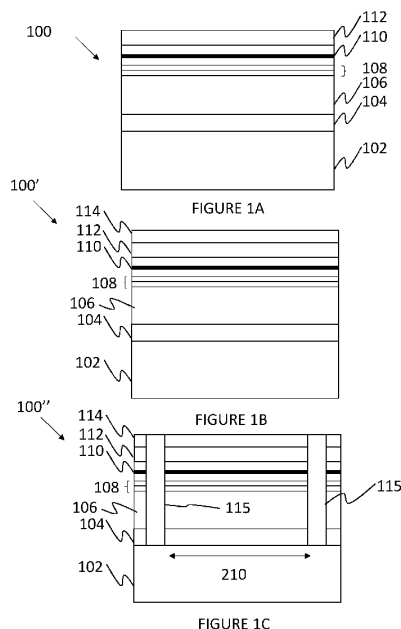
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(54) Title: HIGH RESOLUTION MONOLITHIC RGB ARRAYS



(57) Abstract: A light emitting diode structure comprising a p-type region an n-type region; and a light emitting region for recombination of carriers injectable by the p-type region and the n-type region, wherein at least one of the n-type region and the p-type region is at least partially formed in a via passing through the light emitting region, wherein the via defines the perimeter of a light emitting surface of at least one pixel.

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